QPC: 23RAPhD020	AY 23	Reg. No								
THE REPORT OF TH	GIET UNIVERSI Ph.D. (Second Semest PPEEC20	,	ions,	Apr	ril –	2024				
Time: 3 hrs					Μ	axim	um: ′	70 N	Marks	
7	The figures in the right-hand m	argin indicate n	narks.							
<u>Answer ANY FIVE Questions</u> (14 x 5 = 70 Ma				Ma	rks)					
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	gram and solid solubility in solubility in solution and solid solution devi		ubstra	tes.	How	do do	crysta	al	14	
2. Explain the process o	f silicon oxidation in IC fab	rication. Discus	ss the	kine	etics	of g	rowtl	h,	14	

	defects affect the performance of semiconductor devices?
2.	Explain the process of silicon oxidation in IC fabrication. Discuss the kinetics of growth,
	properties of silicon dioxide, and the importance of high-k and low-k dielectrics.

- 3. Discuss the nature of diffusion in semiconductor materials. How is diffusion used to introduce 14 impurities into semiconductor substrates?
- 4. Describe the different etching techniques employed in semiconductor processing. How do wet 14 chemical etching, dry physical etching, and reactive ion etching differ?
- 5. What are the key features and advantages of silicon bipolar technologies? Discuss second-14 order effects in bipolar transistors and the performance of BiCMOS technology.
- Explain the fabrication of SOI (Silicon-on-Insulator) technology using different methods such 6. 14 as SIMOX and Smart Cut. What are the advantages of SOI technology?
- 7. Discuss the different epitaxy techniques used in semiconductor manufacturing. How are 14 molecular beam epitaxy, vapour phase epitaxy, and liquid phase epitaxy evaluated for quality?
- 8. What are the key considerations in ion implantation in semiconductor processing? Discuss 14 penetration range, process considerations, and the effects of implantation damage.